SEMICONDUCTORS

Type 2N4261 Geometry 0014 **Polarity PNP Qual Level: JAN - JANS**

Features:

- Fast switching small signal silicon transistor.
- Housed in a TO-72 case.
- Also available in chip form using the 0014 chip geometry.
- The Min and Max limits shown are per MIL-PRF-19500/511 which Semicoa meets in all cases.
- Radiation graphs available.

Maximum Ratings

 $T_{C} = 25^{\circ}C$ unless otherwise specified

Rating	Symbol	Rating	Unit	
Collector-Emitter Voltage	V_{CEO}	15	V	
Collector-Base Voltage	V _{CBO}	15	V	
Emitter-Base Voltage	V _{EBO}	4.5	V	
Collector Current, Continuous	Ι _C	30	mA	
Operating Junction Temperature	TJ	-65 to +200	°C	
Storage Temperature	T _{STG}	-65 to +200	℃	

Data Sheet No. 2N4261

Generic Part Number: 2N4261

REF: MIL-PRF-19500/511

Request Quotation







Electrical Characteristics

$T_{\rm C} = 25^{\circ}$ C unless otherwise specified	$T_{\rm C} = 25^{\circ}$ C unless other	erwise specif	ied
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OFF Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage $I_{C} = 10 \ \mu A$	V _{(BR)CBO}	15		V
Collector-Emitter Breakdown Voltage $I_{C} = 10 \text{ mA}$	V _{(BR)CEO}	15		V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	4.5		V
	I _{CEX1} I _{CEX2} I _{CEX3}		50 5.0 5.0	nA nA μA
Base Cutoff Current $V_{CE} = 10 \text{ V}, \text{ V}_{EB} = 2.0 \text{ V}$	I _{BEX}		5.0	nA
Emitter-Base Cutoff Current $V_{EB} = 4.5 V$	I _{EBO}		10	μA

ON Characteristics	Symbol	Min	Max	Unit
Forward current Transfer Ratio				
$I_{C} = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	h _{FE1}	25		
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 1.0 V, pulsed	h _{FE2}	30	150	
$I_{C} = 30 \text{ mA}, V_{CE} = 1.0 \text{ V pulsed}$	h _{FE3}	20		
$I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}, T_{A} = -55^{\circ}C$	h _{FE4}	15		
Collector-Emitter Saturation Voltage				
$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$	V _{CE(sat)1}		0.15	V dc
$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$	V _{CE(sat)2}		0.35	V dc
Base-Emitter Saturation Voltage				
$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	V _{BE1}		0.8	V dc
$V_{CE} = 1.0 \text{ V}, I_C = 10 \text{ mA}$	V_{BE2}		1.0	V dc

Small Signal Characteristics	Symbol	Min	Max	Unit
Magnitude of Common Emitter Small Signal				
Short Circuit Forward Current Transfer Ratio				
V_{CE} = 4.0 V, I_{C} = 5.0 mA, f = 100 MHz	h _{fe1}	15		
$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}, f = 100 \text{ MHz}$	h _{fe2}	20		
Open Circuit Output Capacitance	C _{OBO}		2.5	٦a
$V_{CB} = 4.0 \text{ V}, I_E = 0, 100 \text{ kHz} < f < 1 \text{ MHz}$	OBO		2.5	ρı
Input Capacitance, Output Open Circuited	C _{IBO}		2.5	'nĒ
$V_{EB} = 0.5 \text{ V}, I_{C} = 0, 100 \text{ kHz} < f < 1 \text{ MHz}$	CIBO		2.5	pF

Switching Characteristics	Symbol	Min	Max	Unit
Collector-Base Time Constant $V_{CE} = 4.0 \text{ V}, I_C = 5.0 \text{ mA}, f = 31.8 \text{ MHz}$	r'b'C _{C1}		60	ps
Collector-Base Time Constant $V_{CE} = 4.0 \text{ V}, I_C = 10 \text{ mA}, f = 31.8 \text{ MHz}$	r'b'C _{C2}		50	ps
Saturated Tum On Switching Time to 90% V_{CC} = 17 V, 50 ohm pulse generator	t _{ON}		2.5	ns
Saturated Turn Off Switching Time to 10% V_{CC} = 17 V, 50 ohm pulse generator	t _{OFF}		3.5	ns